

EUROPEAN PATENT OFFICE

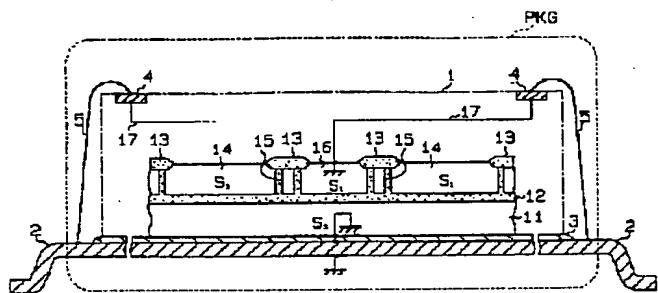
Patent Abstracts of Japan

PUBLICATION NUMBER : 07335811
 PUBLICATION DATE : 22-12-95

APPLICATION DATE : 10-06-94
 APPLICATION NUMBER : 06129324

PHA 23. 843 Wd	MAI. DOSSIER
-------------------	-----------------

APPLICANT : NIPPONDENSO CO LTD;
 INVENTOR : FUJINO SEIJI;
 INT.CL. : H01L 23/50 H01L 21/60 H01L 23/34
 TITLE : SEMICONDUCTOR DEVICE



ABSTRACT : PURPOSE: To improve heat radiation efficiency of a semiconductor device which incorporates a semiconductor chip having an SOI(Silicon On Insulator) structure without increasing a package size and cost.

CONSTITUTION: A semiconductor chip 1 having an SOI structure is bonded to a die pad 2 in the state where the back surface of a semiconductor substrate 11 of the semiconductor chip 1 is set to reference potential and electric conduction is kept between the back surface of the semiconductor substrate 11 and the lead frame (die pad) 2. In contrast, there is provided a heat dissipation pad 4 on the surface of the semiconductor chip 1 where electric conduction is kept with a part (buffer region 16) set to reference potential on an insulating film 12 inside the surface. The heat radiation pad 4 and the lead frame (external connection lead part) 2 are electrically connected with each other through a heat radiation lead wire 5, and hence heat produced on the insulating film 12 is dissipated on the lead frame 2 through the heat radiation pad 4 and the heat radiation lead wire 5.

COPYRIGHT: (C)1995,JPO